Darlington Amplifier Transistors

NPN Silicon

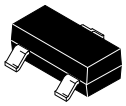
MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

ON Semiconductor®

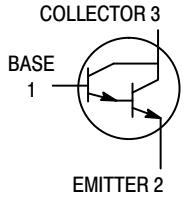
www.onsemi.com

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*



SOT−23 (TO−236)
CASE 318
STYLE 6



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CES}	30	Vdc
Collector − Base Voltage	V_{CBO}	30	Vdc
Emitter − Base Voltage	V_{EBO}	10	Vdc
Collector Current − Continuous	I_C	300	mAdc

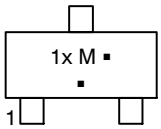
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR− 5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR− 5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

MARKING DIAGRAM



1x = Device Code
x = M for MMBTA13LT1G, SMMBTA13LT1G
x = N for MMBTA14LT1G, SMMBTA14LT1G, T3G
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBTA13LT1G, SMMBTA13LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBTA14LT1G, SMMBTA14LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBTA14LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I_C = 100 μAdc, V_{BE} = 0)	$V_{(BR)CES}$	30	–	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	–	100	nAdc
Emitter Cutoff Current (V_{EB} = 10 Vdc, I_C = 0)	I_{EBO}	–	100	nAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}			–
MMBTA13, SMMBTA13		5000	–	
MMBTA14, SMMBTA14		10,000	–	
(I_C = 100 mAdc, V_{CE} = 5.0 Vdc)				
MMBTA13, SMMBTA13		10,000	–	
MMBTA14, SMMBTA14		20,000	–	
Collector – Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 0.1 mAdc)	$V_{CE(sat)}$	–	1.5	Vdc
Base – Emitter On Voltage (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	V_{BE}	–	2.0	Vdc
SMALL – SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (Note 4) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	f_T	125	–	MHz

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
4. $f_T = |h_{fe}| \bullet f_{test}$.

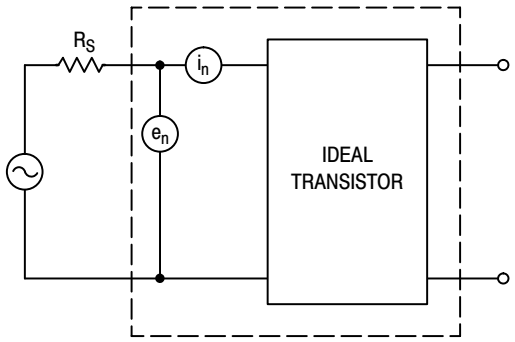


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

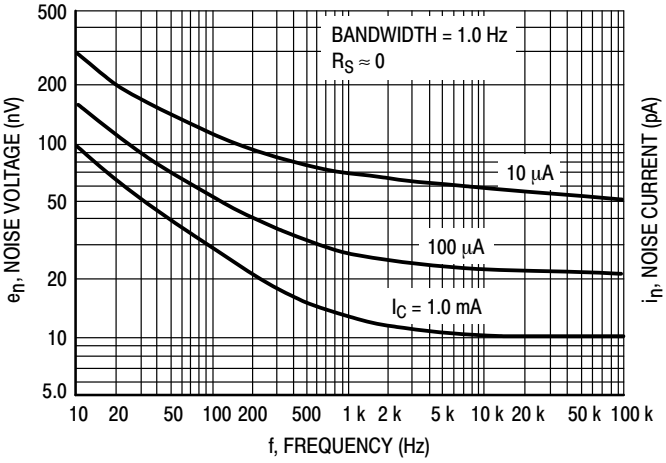


Figure 2. Noise Voltage

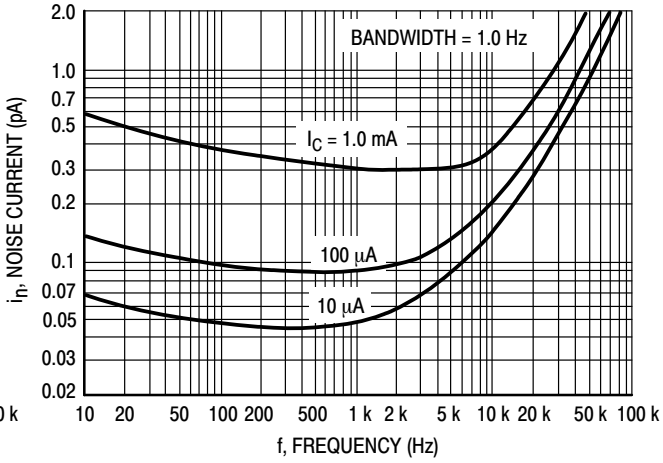


Figure 3. Noise Current

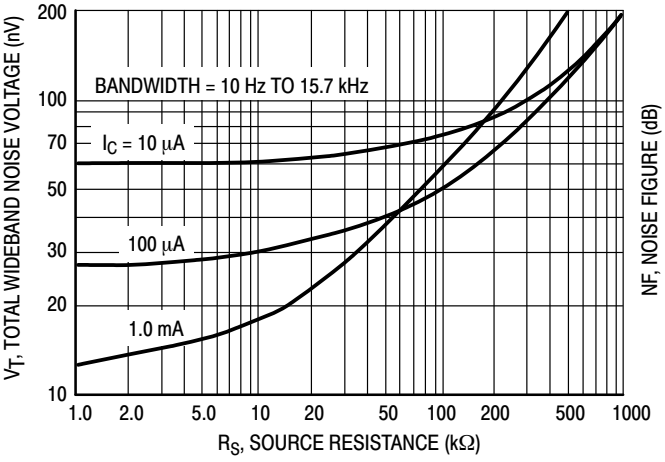


Figure 4. Total Wideband Noise Voltage

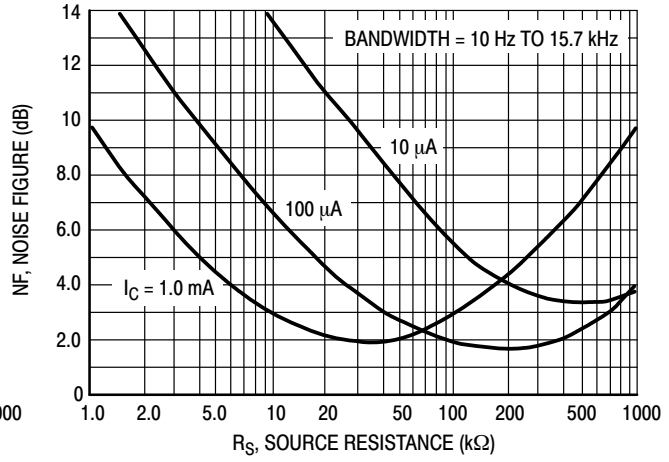


Figure 5. Wideband Noise Figure

SMALL−SIGNAL CHARACTERISTICS

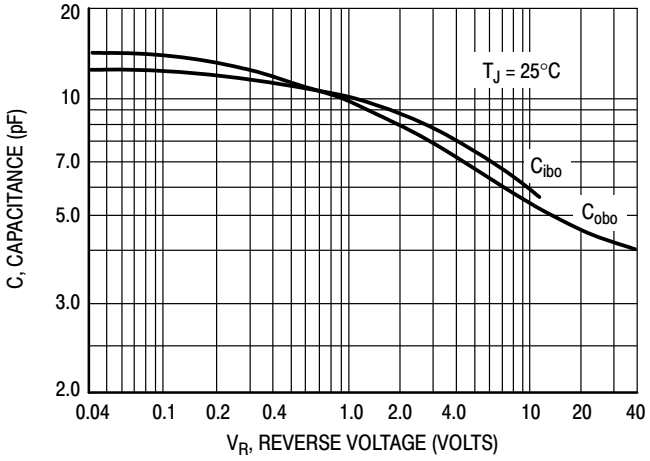


Figure 6. Capacitance

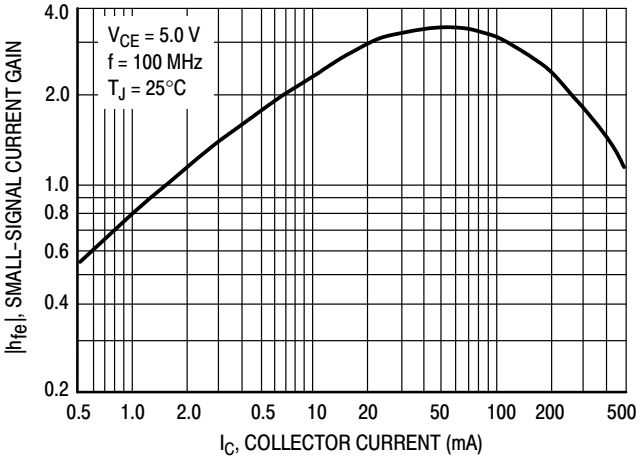


Figure 7. High Frequency Current Gain

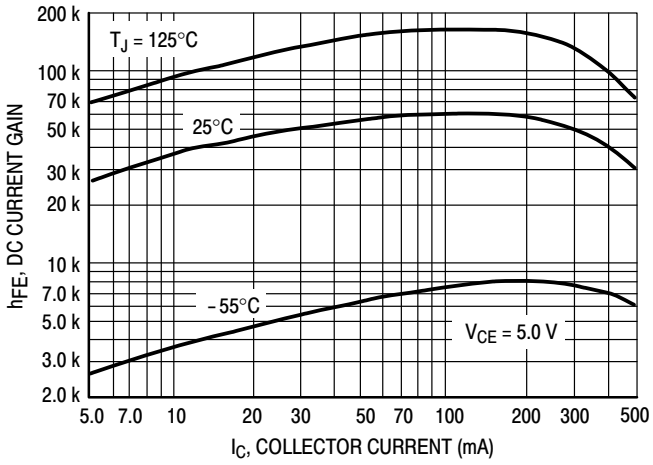


Figure 8. DC Current Gain

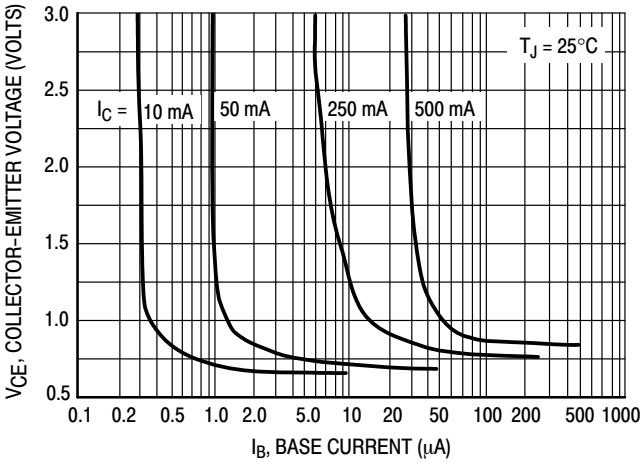


Figure 9. Collector Saturation Region

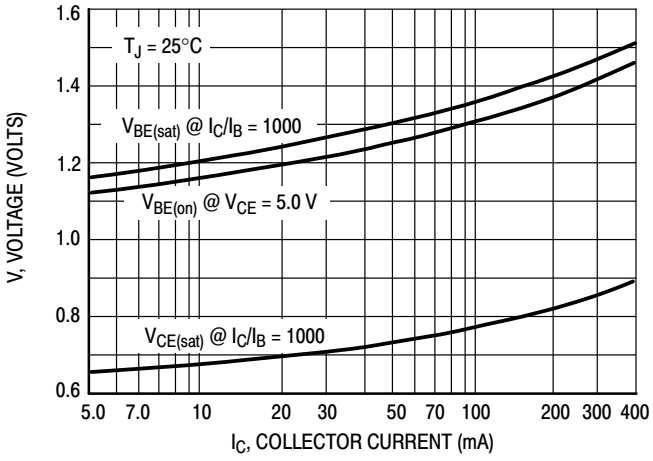


Figure 10. “On” Voltages

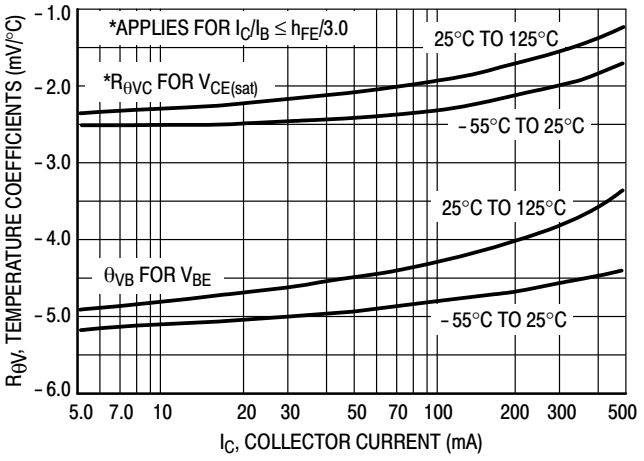


Figure 11. Temperature Coefficients

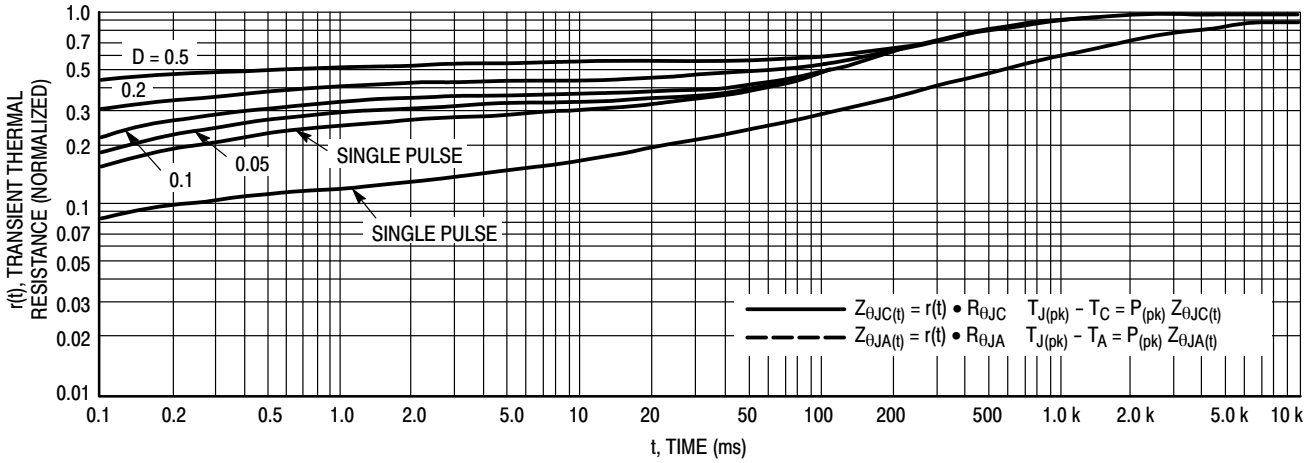


Figure 12. Thermal Response

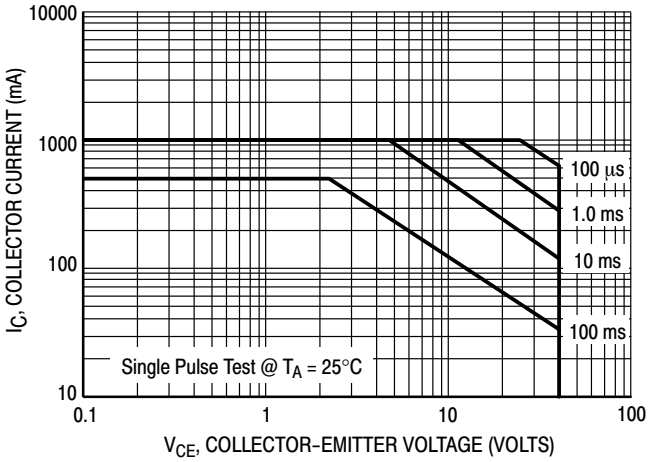
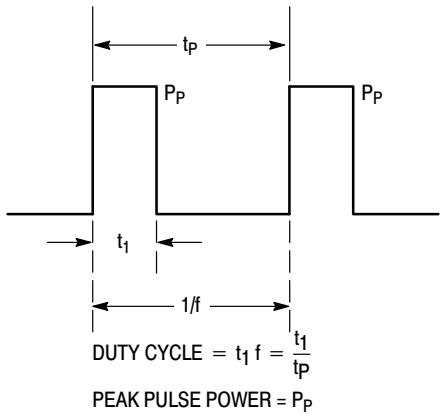


Figure 13. Active Region Safe Operating Area

FIGURE A



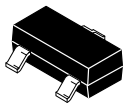
DUTY CYCLE = $t_1 f = \frac{t_1}{t_P}$

PEAK PULSE POWER = P_P

Design Note: Use of Transient Thermal Resistance Data

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

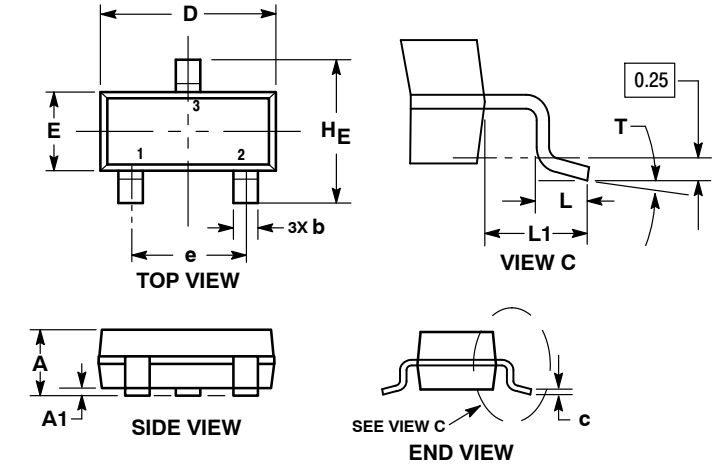
ON Semiconductor®



SOT−23 (TO−236)
CASE 318−08
ISSUE AS

DATE 30 JAN 2018

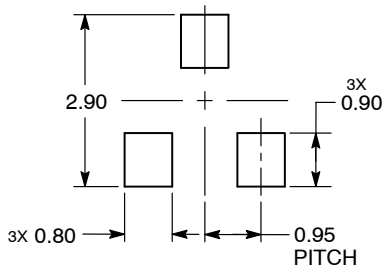
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

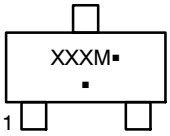
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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